BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

As rescanning documents *will not* correct images, please do not report the images to the Image Problem Mailbox.

09/652,619

WEST

Help | Logout | Interrupt

Main Menu | Search Form | Posting Counts | Show S Numbers | Edit S Numbers | Preferences | Cases

Search Results -

Terms	Documents
metallization and liners and voltage and (surface near2 potentials)	4

Database: US Patents Full-Text Database
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
EPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search: L1

Refine Search

Recall Text | Clear

Search History

DATE: Monday, April 22, 2002 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT; PLUR=YES; OP=OR			
L1	metallization and liners and voltage and (surface near2 potentials)	4	L1

END OF SEARCH HISTORY

WEST

Generate Collection | Print

Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 6143593 A

L1: Entry 1 of 4 File: USPT Nov 7, 2000

US-PAT-NO: 6143593
DOCUMENT-IDENTIFIER: US 6143593 A

TITLE: Elevated channel MOSFET

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Desc | Image

2. Document ID: US 5834371 A

L1: Entry 2 of 4 File: USPT Nov 10, 1998

US-PAT-NO: 5834371
DOCUMENT-IDENTIFIER: US 5834371 A

TITLE: Method and apparatus for preparing and metallizing high aspect ratio silicon semiconductor device contacts to reduce the resistivity thereof

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Desc | Image

3. Document ID: US 3681667 A

L1: Entry 3 of 4 File: USPT Aug 1, 1972

US-PAT-NO: 3681667
DOCUMENT-IDENTIFIER: US 3681667 A

TITLE: CONTROLLED RECTIFIER AND TRIAC WITH LATERALLY OFF-SET GATE AND AUXILIARY SEGMENTS FOR ACCELERATED TURN ON

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw Desc | Image

4. Document ID: US 3586932 A

L1: Entry 4 of 4 File: USPT Jun 22, 1971

US-PAT-NO: 3586932
DOCUMENT-IDENTIFIER: US 3586932 A

TITLE: FIVE LAYER GATE CONTROLLED THYRISTOR WITH NOVEL TURN ON CHARACTERISTICS

Generate Collection | Print

Terms	Documents
metallization and liners and voltage and (surface near2 potentials)	4

Display Format: TI | Change Format

Previous Page Next Page

WEST

Generate Collection | Print

Search Results - Record(s) 1 through 3 of 3 returned.

1. Document ID: US 6143593 A

L3: Entry 1 of 3 File: USPT Nov 7, 2000

US-PAT-NO: 6143593
DOCUMENT-IDENTIFIER: US 6143593 A

TITLE: Elevated channel MOSFET

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw. Desc | Image

2. Document ID: US 6054013 A

L3: Entry 2 of 3 File: USPT Apr 25, 2000

US-PAT-NO: 6054013
DOCUMENT-IDENTIFIER: US 6054013 A

TITLE: Parallel plate electrode plasma reactor having an inductive antenna and adjustable radial distribution of plasma ion density

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw. Desc | Image

3. Document ID: US 6036878 A

L3: Entry 3 of 3 File: USPT Mar 14, 2000

US-PAT-NO: 6036878
DOCUMENT-IDENTIFIER: US 6036878 A

TITLE: Low density high frequency process for a parallel-plate electrode plasma reactor having an inductive antenna

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw. Desc | Image

Generate Collection | Print

Terms	Documents
L2 and (germanium and undoped and doped and nitride)	3

Display Format: TI Change Format

Previous Page Next Page

WEST

Help | Logout | Interrupt

Main Menu | Search Form | Posting Counts | Show S Numbers | Edit S Numbers | Preferences | Cases

Search Results -

Terms	Documents
L2 and (germanium and undoped and doped and nitride)	3

Database: US Patents Full-Text Database
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
EPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search: L3

Refine Search

Recall Text | Clear

Search History

DATE: Monday, April 22, 2002 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
	DB=USPT; PLUR=YES; OP=OR		
L3	L2 and (germanium and undoped and doped and nitride)	3	L3
L2	(plugs or vias or interconnects or holes) and liners and voltage and (surface near2 potentials)	99	L2
L1	metallization and liners and voltage and (surface near2 potentials)	4	L1

END OF SEARCH HISTORY

WEST

Help | Logout | Interrupt

09/653,619

Main Menu | Search Form | Posting Counts | Show S Numbers | Edit S Numbers | Preferences | Cases

Search Results -

Terms	Documents
L3 and doped and undoped	6

Database: US Patents Full-Text Database
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
EPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search: L4

Refine Search

Recall Text | Clear

Search History

DATE: Monday, April 22, 2002 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT; PLUR=YES; OP=OR			
L4	L3 and doped and undoped	6	L4
L3	L1 and polysilicon and metallization	41	L3
L2	L1 and polysilicon a	6254293	L2
L1	((via or contact or hole) near4 lining)	4374	L1

END OF SEARCH HISTORY

WEST

Generate Collection | Print

Search Results - Record(s) 1 through 6 of 6 returned.

☐ 1. Document ID: US 6369430 B1

L4: Entry 1 of 6 File: USPT Apr 9, 2002

US-PAT-NO: 6369430
DOCUMENT-IDENTIFIER: US 6369430 B1

TITLE: Method of preventing two neighboring contacts from a short-circuit caused by a void between them and device having the same

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. Desc | Image

☐ 2. Document ID: US 6171952 B1

L4: Entry 2 of 6 File: USPT Jan 9, 2001

US-PAT-NO: 6171952
DOCUMENT-IDENTIFIER: US 6171952 B1

TITLE: Methods of forming metallization layers and integrated circuits containing such

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw. Desc | Image

☐ 3. Document ID: US 6090636 A

L4: Entry 3 of 6 File: USPT Jul 18, 2000

US-PAT-NO: 6090636
DOCUMENT-IDENTIFIER: US 6090636 A

TITLE: Integrated circuits using optical waveguide interconnects formed through a semiconductor wafer and methods for forming same

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw. Desc | Image

☐ 4. Document ID: US 5994215 A

L4: Entry 4 of 6 File: USPT Nov 30, 1999

US-PAT-NO: 5994215
DOCUMENT-IDENTIFIER: US 5994215 A

TITLE: Method for suppression pattern distortion associated with BPSG reflow

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC
Draw Desc | Image

☐ 5. Document ID: US 5895261 A

L4: Entry 5 of 6 File: USPT Apr 20, 1999

US-PAT-NO: 5895261
DOCUMENT-IDENTIFIER: US 5895261 A

TITLE: Process for making integrated circuit structure comprising local area interconnects formed over semiconductor substrate by selective deposition on seed layer in patterned trench

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC
Draw Desc | Image

☐ 6. Document ID: US 5670425 A

L4: Entry 6 of 6 File: USPT Sep 23, 1997

US-PAT-NO: 5670425
DOCUMENT-IDENTIFIER: US 5670425 A

TITLE: Process for making integrated circuit structure comprising local area interconnects formed over semiconductor substrate by selective deposition on seed layer in patterned trench

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC
Draw Desc | Image

Generate Collection | Print

Terms	Documents
L3 and doped and undoped	6

Display Format: TI Change Format

Previous Page Next Page